

S71VS/XS-R Memory Subsystem Solutions

**MirrorBit® 1.8 Volt-Only Simultaneous Read/Write,
Burst Mode Multiplexed Flash Memory and Burst Mode
pSRAM**

**256/128/64 Mb (16/8/4 Mb x 16-bit) Flash,
128/64/32 Mb (8/4/2 Mb x 16-bit) pSRAM**

Data Sheet



Notice to Readers: This document states the current technical specifications regarding the Spansion product(s) described herein. Each product described herein may be designated as Advance Information, Preliminary, or Full Production. See [Notice On Data Sheet Designations](#) for definitions.

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Combination

Some data sheets contain a combination of products with different designations (Advance Information, Preliminary, or Full Production). This type of document distinguishes these products and their designations wherever necessary, typically on the first page, the ordering information page, and pages with the DC Characteristics table and the AC Erase and Program table (in the table notes). The disclaimer on the first page refers the reader to the notice on this page.

Full Production (No Designation on Document)

When a product has been in production for a period of time such that no changes or only nominal changes are expected, the Preliminary designation is removed from the data sheet. Nominal changes may include those affecting the number of ordering part numbers available, such as the addition or deletion of a speed option, temperature range, package type, or V_{IO} range. Changes may also include those needed to clarify a description or to correct a typographical error or incorrect specification. SpanSion Inc. applies the following conditions to documents in this category:

"This document states the current technical specifications regarding the SpanSion product(s) described herein. SpanSion Inc. deems the products to have been in sufficient production volume such that subsequent versions of this document are not expected to change. However, typographical or specification corrections, or modifications to the valid combinations offered may occur."

Questions regarding these document designations may be directed to your local sales office.

S71VS/XS-R Memory Subsystem Solutions

MirrorBit® 1.8 Volt-Only Simultaneous Read/Write, Burst Mode Multiplexed Flash Memory and Burst Mode pSRAM

**256/128/64 Mb (16/8/4 Mb x 16-bit) Flash,
128/64/32 Mb (8/4/2 Mb x 16-bit) pSRAM**

Data Sheet



Features

- Power supply voltage of 1.7V to 1.95V
- Flash / pSRAM Burst Speed: 108 MHz, 104 MHz, 83 MHz
- MCP BGA Packages
 - 52 ball, 6.0 x 5.0 mm, 0.5 mm ball pitch
 - 56 ball, 7.7 x 6.2 mm, 0.5 mm ball pitch
 - 56 ball, 9.2 x 8.0 mm, 0.5 mm ball pitch
- Operating Temperature
 - Wireless, –25°C to +85°C
 - Industrial, –40°C to +85°C

General Description

The S71VS-R Series is a product line of stacked Multi-Chip Package (MCP) memory solutions and consists of the following items:

- One or more S29VS-R Flash memory die
- One or more pSRAM

The products covered by this document are listed in the table below. For details about their specifications, please refer to their individual data sheet for further details.

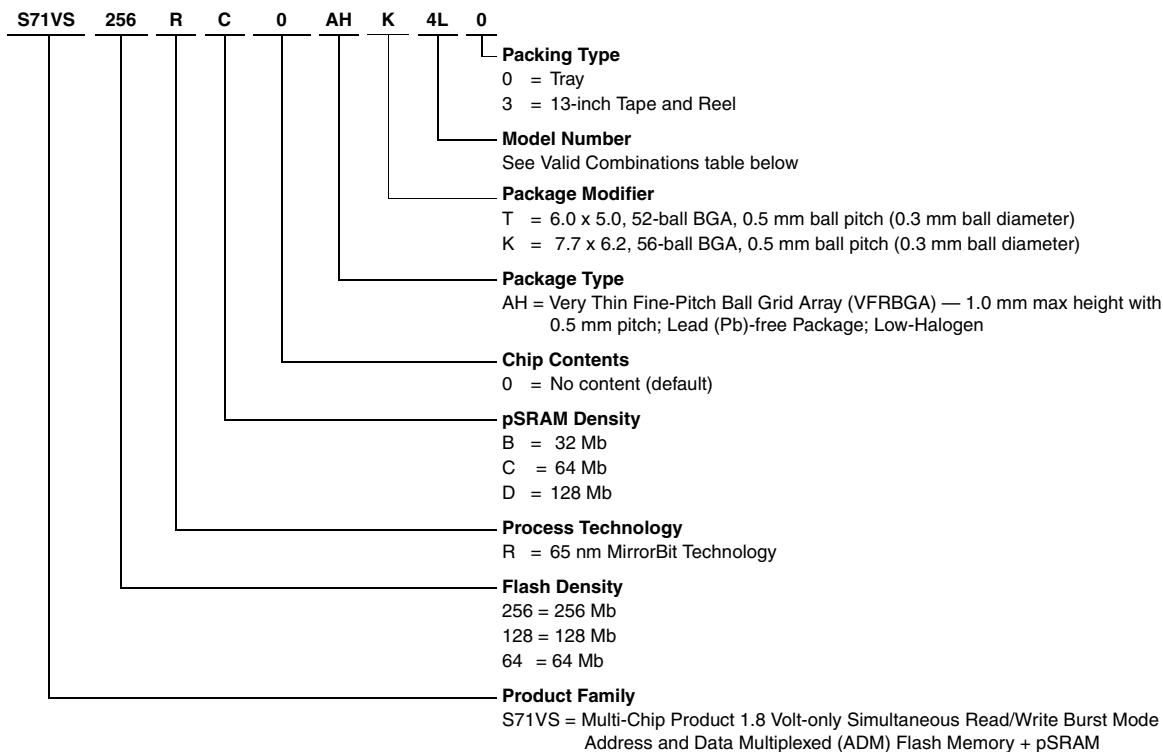
Flash Density	pSRAM Density	Product
64 Mb	32 Mb	S71VS064RB0
128 Mb	32 Mb	S71VS128RB0
128 Mb	64 Mb	S71VS128RC0
256 Mb	64 Mb	S71VS256RC0
256 Mb	128 Mb	S71VS256RD0

For detailed specifications, please refer to the individual data sheets:

Document	Publication Identification Number
S29VS/XS-R	S29VS_XS-R_00
S29VS/XS-R Supplement	S29VS_XS-R_SP
S29VS064R/XS064R	S29VS_XS064R_00
S29VS064R/XS064R Supplement	S29VS064R_XS064R_SP
128 Mb MUX pSRAM Type 5	pSRAM_39
32 Mb CellularRAM Address/Data multiplexed	SWM032D108M1R
32 Mb CellularRAM Address/Data multiplexed	SWM032D108M3R
64 Mb CellularRAM Address/Data multiplexed	SWM064D108M1R
128 Mb CellularRAM Address/Data multiplexed	SWM128D108M1R
128 Mb CellularRAM Address/Data multiplexed	SWM128D108M3R

1. Ordering Information

The order number is formed by a valid combinations of the following:



1.1 Valid Combinations

Valid Combinations list configurations planned to be supported in volume for this device. Consult your local sales office to confirm availability of specific valid combinations and to check on newly released combinations.

Base Ordering Part Number	Package	Model Number	Packing Type	pSRAM Type	Flash Boot	Temperature Range	Flash / pSRAM Speed	Pinout and Package Notes		
S71VS064RB0	AHT	0L	0, 3	SWM032D108M1R	Top	Wireless	108 MHz	Pinout: S71VS-R 52-ball Package: RSE052		
		8L			Bottom			Pinout: S71VS-R 52-ball Package: RLG052		
		3L			Top				Pinout: S71VS-R 52-ball Package: RSE052	
		BL			Bottom			Pinout: S71VS-R 52-ball Package: RSE052		
		4L			Top					Pinout: S71VS-R 52-ball Package: RSE052
		CL			Bottom				Pinout: S71VS-R 52-ball Package: RSE052	
		0M		Top	Industrial	Pinout: S71VS-R 52-ball Package: RSE052				
		8M		Bottom						
		3M		Top				Pinout: S71VS-R 52-ball Package: RLG052		
		BM		Bottom						
S71VS128RB0	AHK	0L		SWM032D108M1R	Top	Wireless	108 MHz	Pinout: S71VS-R 56-ball Package: RLA056		
		8L			Bottom				Pinout: S71VS-R 56-ball Package: RSD056	
		3L			Top			Pinout: S71VS-R 56-ball Package: RSD056		
		BL			Bottom					Pinout: S71VS-R 56-ball Package: RSD056
		4L			Top					
		CL			Bottom				Pinout: S71VS-R 56-ball Package: RSD056	
S71VS128RC0	AHK	SWM064D108M1R		Top	108 MHz		Pinout: S71VS-R 56-ball Package: RSD056			
				CL				Bottom		
S71VS256RC0	AHK	SWM064D108M1R		Top	108 MHz		Pinout: S71VS-R 56-ball Package: RLA056			
				CL				Bottom		
S71VS256RD0	AHK	3L		SWM128D108M1R	Top		108 MHz	Pinout: S71VS-R 56-ball Package: RSD056		
		BL			Bottom				83 MHz	
		3C			Top		83 MHz			
		BC			Bottom				83 MHz	
		3M		SWM128D108M3R	Top	Industrial	108 MHz			
		40		MUX pSRAM Type 5	Top	Wireless	108/104 MHz			
		C0			Bottom					

Note:

If a choice exists, SpanSion recommends Top Boot.

2. Input/Output Descriptions

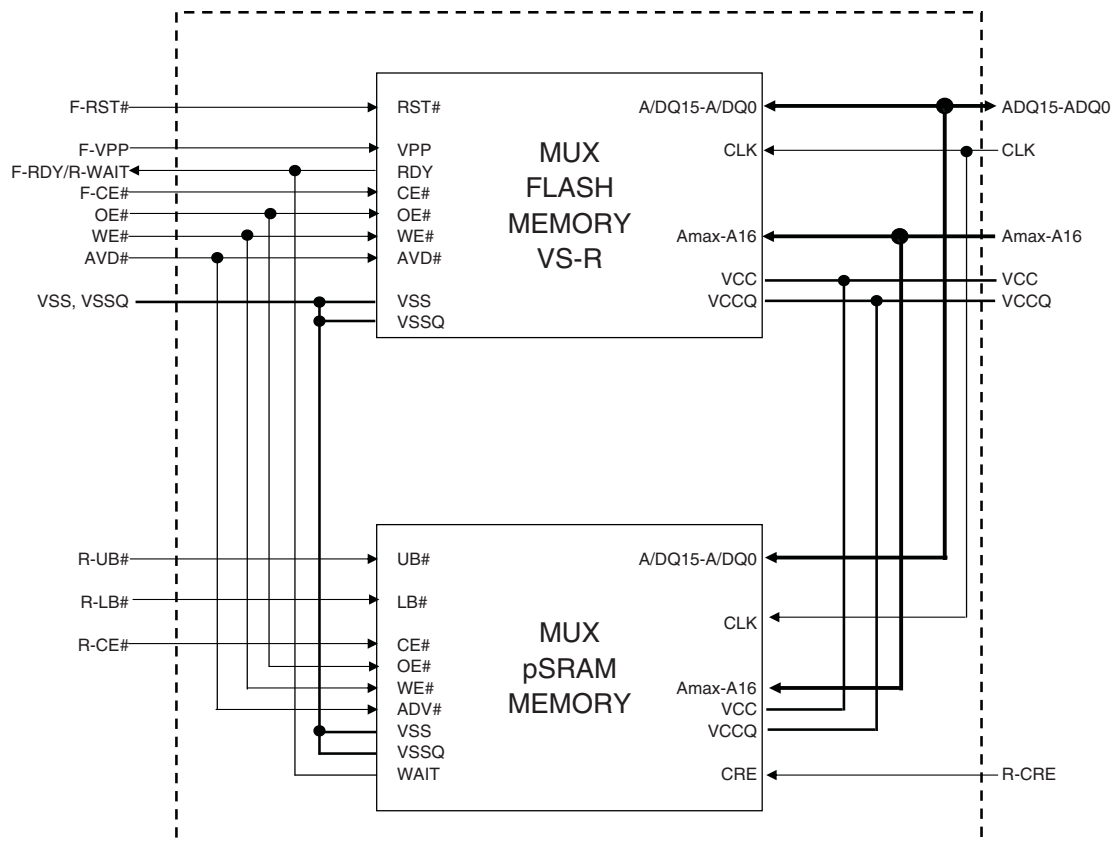
Table 2.1 identifies the input and output package connections provided on the device.

Table 2.1 Input/Output Descriptions

Symbol	Description	Flash	RAM
AMAX – A16	Address inputs.	X	X
A/DQ15-A/DQ0	Multiplexed Address/Data.	X	X
AVD#	Address Valid input. Indicates to device that the valid address is present on the address inputs. Low = for asynchronous mode, indicates valid address; for burst mode, causes starting address to be latched. High = device ignores address inputs	X	X
CLK	Clock input. In burst mode, after the initial word is output, subsequent active edges of CLK increment the internal address counter. Should be at V_{IL} or V_{IH} while in asynchronous mode.	X	X
DNU	Do Not Use. A device internal signal may be connected to the package connector. The connection may be used by Spansion for test or other purposes and is not intended for connection to any host system signal. Any DNU signal related function will be inactive when the signal is at V_{IL} . The signal has an internal pull-down resistor and may be left unconnected in the host system or may be tied to V_{SS} . Do not use these connections for PCB signal routing channels. Do not connect any host system signal to these connections.		
OE#	Output Enable input. Asynchronous relative to CLK for the Burst mode.	X	X
F-CE#	Chip-enable input for Flash. Asynchronous relative to CLK for Burst Mode.	X	
F-RDY/R-WAIT	Ready output; indicates the status of the Burst read. Flash Memory RDY (using default "Active HIGH" configuration) V_{OL} = data invalid V_{OH} = data valid Note: The default polarity for the pSRAM WAIT signal is opposite the default polarity of the Flash RDY signal. pSRAM WAIT (using default "Active HIGH" configuration) V_{OL} = data valid V_{OH} = data invalid To match polarities, change bit 10 of the pSRAM Bus Configuration Register to 0 (Active LOW WAIT). Alternately, change bit 10 of the Flash Configuration Register to 0 (Active LOW RDY).	X	X
F-RST#	Hardware reset input. Low = device resets and returns to reading array data	X	
F- V_{PP}	Accelerated input. At V_{HH} , accelerates programming; automatically places device in unlock bypass mode. At V_{IL} , disables all program and erase functions. Should be at V_{IH} for all other conditions.	X	
NC	Not Connected. No device internal signal is connected to the package connector nor is there any future plan to use the connector for a signal. The connection may safely be used for routing space for a signal on a Printed Circuit Board (PCB).		
R-CE#	Chip-enable input for pSRAM.		X
R-CRE	Control Register Enable (pSRAM).		X
R-LB#	Lower Byte Control (pSRAM).		X
R-UB#	Upper Byte Control (pSRAM).		X
RFU	Reserved For Future Use. No device internal signal is currently connected to the package connector but there is potential future use for the connector for a signal. It is recommended to not use RFU connectors for PCB routing channels so that the PCB may take advantage of future enhanced features in compatible footprint devices.		
V_{CC}	Flash and pSRAM 1.8 Volt-only single power supply.	X	X
V_{CCQ}	Flash and pSRAM Input/Output Power Supply.	X	X
V_{SS}	Ground.	X	X
V_{SSQ}	Input/Output Ground.	X	X
WE#	Write Enable input.	X	X

3. MCP Block Diagram

Figure 3.1 S71VS-R MCP Block Diagram



4. Connection Diagrams/Physical Dimensions

This section contains the I/O designations and package specifications for the S71VS-R.

4.1 Special Handling Instructions for FBGA Packages

Special handling is required for Flash Memory products in FBGA packages.

Flash memory devices in FBGA packages may be damaged if exposed to ultrasonic cleaning methods. The package and/or data integrity may be compromised if the package body is exposed to temperatures above 150°C for prolonged periods of time.

4.2 Connection Diagrams

Figure 4.1 S71VS-R 56-ball Fine-Pitch Ball Grid Array

(Top View, Balls Facing Down)

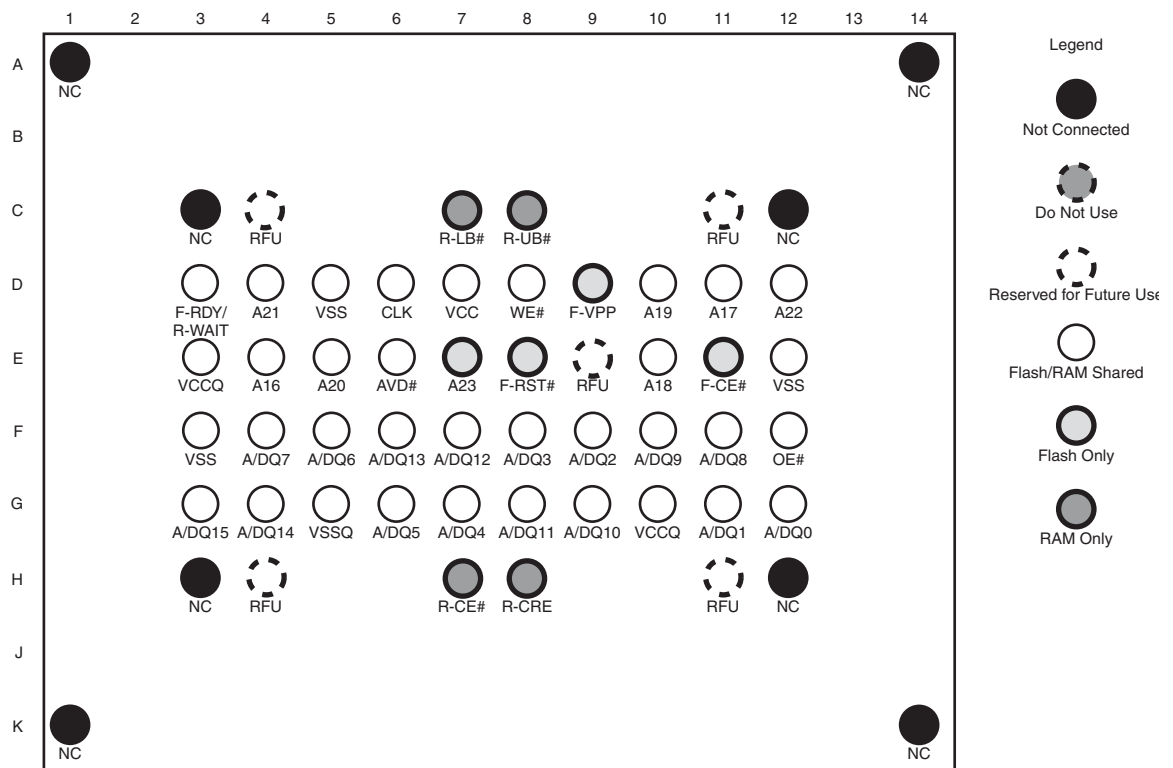
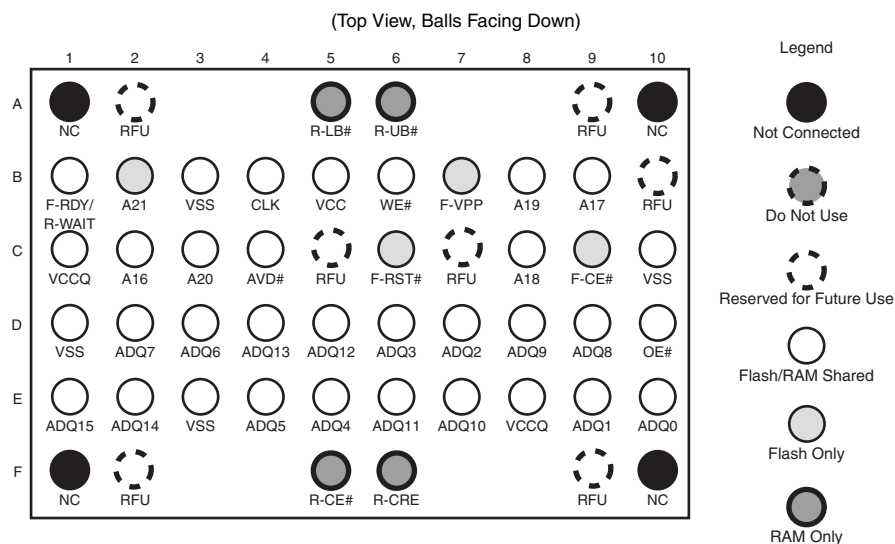


Figure 4.2 S71VS-R 52-ball Fine-Pitch Ball Grid Array



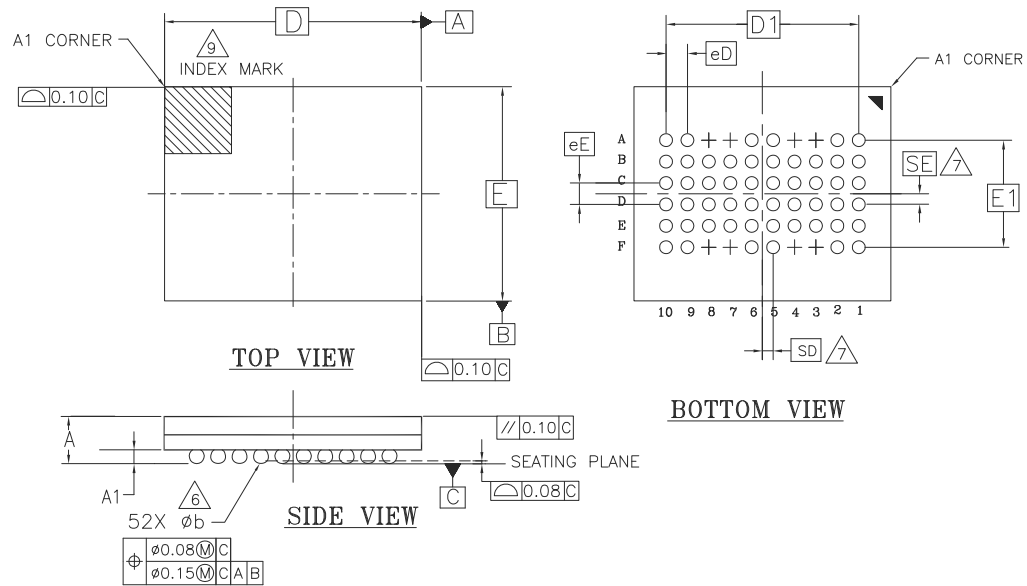
Notes:

- Addresses are shared between Flash and RAM depending on the density of the pSRAM.
- V_{SS} and V_{SSQ} must be connected together.

MCP	Flash-Only Addresses	Shared Addresses	Shared ADQ Pins
S71VS064RB0	A21	A20-A16	A/DQ15-A/DQ0
S71VS128RB0	A22-A21	A20-A16	
S71VS128RC0	A22	A21-A16	
S71VS256RC0	A23-A22	A21-A16	
S71VS256RD0	A23	A22-A16	

4.3 Physical Dimensions

Figure 4.3 RLG052 - 52-ball VFRBGA 6.0 x 5.0 mm



PACKAGE	RLG 052			
JEDEC	N/A			
	6.00 mm x 5.00 mm PACKAGE			
SYMBOL	MIN	NOM	MAX	NOTE
A	---	---	1.00	PROFILE
A1	0.18	---	---	BALL HEIGHT
D	6.00 BSC.			BODY SIZE
E	5.00 BSC.			BODY SIZE
D1	4.50 BSC.			MATRIX FOOTPRINT
E1	2.50 BSC.			MATRIX FOOTPRINT
MD	10			MATRIX SIZE D DIRECTION
ME	6			MATRIX SIZE E DIRECTION
n	52			BALL COUNT
φb	0.25	0.30	0.35	BALL DIAMETER
e	0.50 BSC.			BALL PITCH
SE/SD	0.25 BSC.			SOLDER BALL PLACEMENT
	3A,3F,4A,4F,7A,7F,8A,8F			DEPOPULATED SOLDER BALLS

NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994.
2. ALL DIMENSIONS ARE IN MILLIMETERS.
3. BALL POSITION DESIGNATION PER JEP 95, SECTION 4.3, SPP-010.
4. $\boxed{e}$ REPRESENTS THE SOLDER BALL GRID PITCH.

5. SYMBOL "MD" IS THE BALL MATRIX SIZE IN THE "D" DIRECTION.

SYMBOL "ME" IS THE BALL MATRIX SIZE IN THE "E" DIRECTION.

n IS THE NUMBER OF POPULATED SOLDER BALL POSITIONS FOR MATRIX SIZE MD X ME

6. DIMENSION "b" IS MEASURED AT THE MAXIMUM BALL DIAMETER IN A PLANE PARALLEL TO DATUM C.

7. SD AND SE ARE MEASURED WITH RESPECT TO DATUMS A AND B AND DEFINE THE POSITION OF THE CENTER SOLDER BALL IN THE OUTER ROW.

WHEN THERE IS AN ODD NUMBER OF SOLDER BALLS IN THE OUTER ROW SD OR SE = 0.000.

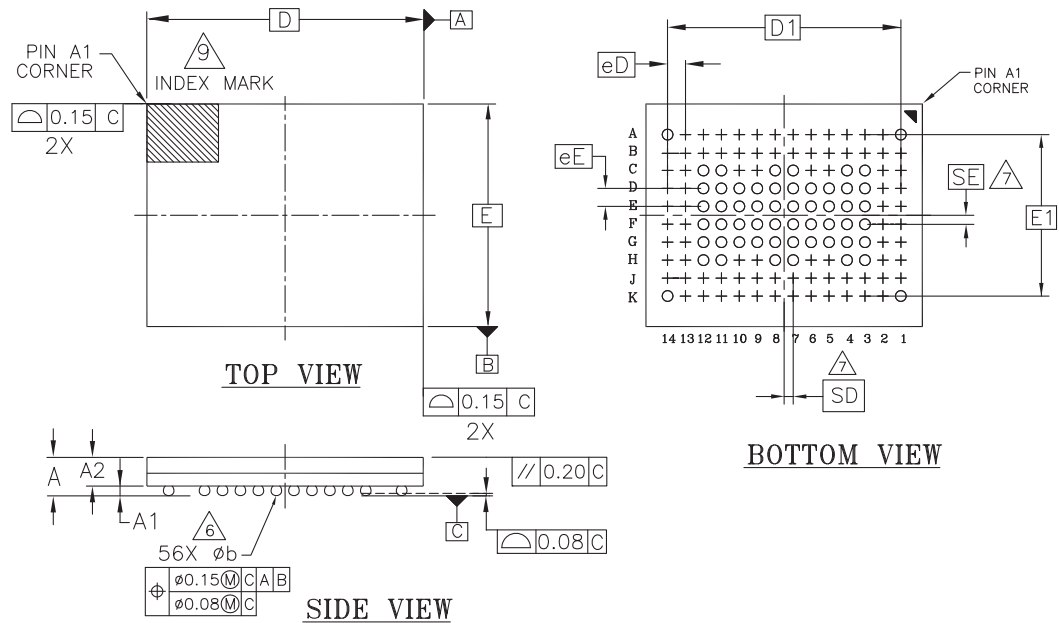
WHEN THERE IS AN EVEN NUMBER OF SOLDER BALLS IN THE OUTER ROW, SD OR SE = $\boxed{e/2}$

8. "+" INDICATES THE THEORETICAL CENTER OF DEPOPULATED BALLS.

9. A1 CORNER TO BE IDENTIFIED BY CHAMFER, LASER OR INK MARK, METALLIZED MARK INDENTATION OR OTHER MEANS.

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Figure 4.5 RSD056—56-ball VFRBGA 7.7 x 6.2 mm



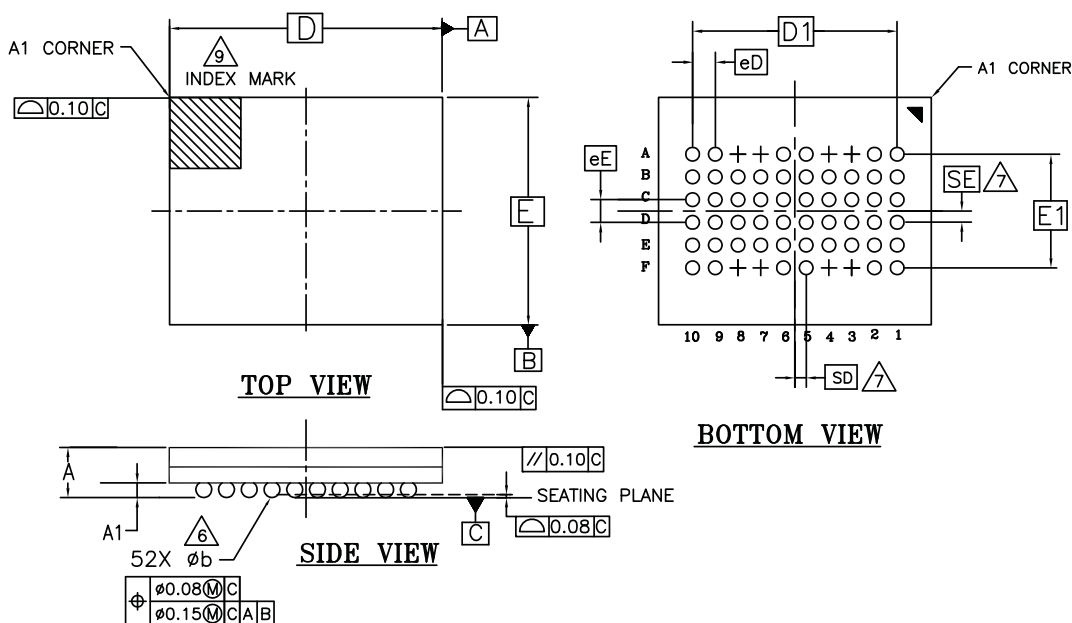
PACKAGE	RSD 056			NOTE
JEDEC	N/A			
D x E	7.70 mm x 6.20 mm PACKAGE			
SYMBOL	MIN	NOM	MAX	
A	0.80	0.90	1.00	PROFILE
A1	0.18	---	---	BALL HEIGHT
A2	0.62	---	0.74	BODY THICKNESS
D	7.70 BSC			BODY SIZE
E	6.20 BSC			BODY SIZE
D1	6.50 BSC			MATRIX FOOTPRINT
E1	4.50 BSC			MATRIX FOOTPRINT
MD	14			MATRIX SIZE D DIRECTION
ME	10			MATRIX SIZE E DIRECTION
n	56			BALL COUNT
Øb	0.25	0.30	0.35	BALL DIAMETER
eE	0.50 BSC			BALL PITCH
eD	0.50 BSC			BALL PITCH
SE SD	0.25 BSC			SOLDER BALL PLACEMENT
A2~A9, B1~B10, C1,C2,C9,10,D1,D2,D9,D10 E1,E2,E3,E8,E9,E10,F1,F2,F3,F9,F10,G1,G2,G9,G10 H1,H2,H9,H10,I1,I2,I3,I8,I9,I10,J1,J2,J3,J8,J9,J10 L1,L2,L3,L10,M1,M2,M9,M10, N1~N10, P2~P9				
DEPOPULATED SOLDER BALLS				

NOTES:

1. DIMENSIONING AND TOLERANCING METHODS PER ASME Y14.5M-1994.
2. ALL DIMENSIONS ARE IN MILLIMETERS.
3. BALL POSITION DESIGNATION PER JEP95, SECTION 4.3, SPP-010.
4. [e] REPRESENTS THE SOLDER BALL GRID PITCH.
5. SYMBOL "MD" IS THE BALL MATRIX SIZE IN THE "D" DIRECTION.
SYMBOL "ME" IS THE BALL MATRIX SIZE IN THE "E" DIRECTION.
n IS THE NUMBER OF POPULATED SOLDER BALL POSITIONS FOR MATRIX SIZE MD X ME.
[6] DIMENSION "b" IS MEASURED AT THE MAXIMUM BALL DIAMETER IN A PLANE PARALLEL TO DATUM C.
[7] SD AND SE ARE MEASURED WITH RESPECT TO DATUMS A AND B AND DEFINE THE POSITION OF THE CENTER SOLDER BALL IN THE OUTER ROW.
WHEN THERE IS AN ODD NUMBER OF SOLDER BALLS IN THE OUTER ROW SD OR SE = 0.000.
WHEN THERE IS AN EVEN NUMBER OF SOLDER BALLS IN THE OUTER ROW, SD OR SE = [e/2]
6. "+" INDICATES THE THEORETICAL CENTER OF DEPOPULATED BALLS.
7. A1 CORNER TO BE IDENTIFIED BY CHAMFER, LASER OR INK MARK, METALLIZED MARK INDENTATION OR OTHER MEANS.
10. OUTLINE AND DIMENSIONS PER CUSTOMER REQUIREMENT.

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Figure 4.6 RSE052—52-ball VFRBGA 6.0 x 5.0 mm



PACKAGE	RSE 052			
JEDEC	N/A			
D X E	6.00 mm x 5.00 mm PACKAGE			
SYMBOL	MIN	NOM	MAX	NOTE
A	---	---	1.00	PROFILE
A1	0.18	---	---	BALL HEIGHT
	6.00 BSC.			BODY SIZE
	5.00 BSC.			BODY SIZE
	4.50 BSC.			MATRIX FOOTPRINT
	2.50 BSC.			MATRIX FOOTPRINT
MD	10			MATRIX SIZE D DIRECTION
ME	6			MATRIX SIZE E DIRECTION
n	52			BALL COUNT
b	0.25	0.30	0.35	BALL DIAMETER
	0.50 BSC.			BALL PITCH
	0.25 BSC.			SOLDER BALL PLACEMENT
	3A,3F,4A,4F,7A,7F,8A,8F			DEPOPULATED SOLDER BALLS

NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994.
2. ALL DIMENSIONS ARE IN MILLIMETERS.
3. BALL POSITION DESIGNATION PER JEP 95, SECTION 4.3, SPP-010.
4. [e] REPRESENTS THE SOLDER BALL GRID PITCH.
5. SYMBOL "MD" IS THE BALL MATRIX SIZE IN THE "D" DIRECTION.

SYMBOL "ME" IS THE BALL MATRIX SIZE IN THE "E" DIRECTION.
n IS THE NUMBER OF POPULATED SOLDER BALL POSITIONS FOR MATRIX SIZE MD X ME

6. DIMENSION "b" IS MEASURED AT THE MAXIMUM BALL DIAMETER IN A PLANE PARALLEL TO DATUM C.

7. SD AND SE ARE MEASURED WITH RESPECT TO DATUMS A AND B AND DEFINE THE POSITION OF THE CENTER SOLDER BALL IN THE OUTER ROW.

WHEN THERE IS AN ODD NUMBER OF SOLDER BALLS IN THE OUTER ROW SD OR SE = 0.000.

WHEN THERE IS AN EVEN NUMBER OF SOLDER BALLS IN THE OUTER ROW, SD OR SE = [e/2]

8. "+" INDICATES THE THEORETICAL CENTER OF DEPOPULATED BALLS.

9. A1 CORNER TO BE IDENTIFIED BY CHAMFER, LASER OR INK MARK, METALLIZED MARK INDENTATION OR OTHER MEANS.

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5. Revision History

Section	Description
Revision 01 (August 25, 2008)	
	Initial release
Revision 02 (November 4, 2008)	
Global	Added OPNs S71VS064RB0AHT00/04/80/84
Connection Diagrams	Added S71VS-R 52-ball connection diagram
Physical Dimensions	Added RSB052
General Description	Changed 128 Mb Mux pSRAM PID from TBD to pSRAM_39
Revision 03 (November 10, 2008)	
General Description	Changed 64 Mb MUX pSRAM Type 3 PID from muxpsram_14 to muxpsram_15
Revision 04 (January 13, 2009)	
Physical Dimensions	Replaced NLD056 with NSD056
Revision 05 (January 23, 2009)	
Valid Combinations	Added OPN S71VS128RC0AHK20
Physical Dimensions	Added RSD056
Revision 06 (March 11, 2009)	
Valid Combinations	Added 108 MHz speed grade to S71VS128RC0 and S71VS256RC0
Revision 07 (September 29, 2009)	
General Description	Added S71VS128RB0; added muxpsram_10
Valid Combinations	Added OPN S71VS128RB0
Revision 08 (April 9, 2010)	
General Description	Added SWM064D108M1R Updated pSRAM documentation names
Valid Combinations	Added OPNs: S71VS128RC0AHK4L S71VS256RC0AHK4L Removed Bottom Boot options
Connection Diagrams	Updated V _{SSQ} ball to V _{SS}
Revision 09 (May 4, 2010)	
General Description	Added reference to S29VS064R data sheet Removed CustComspec_01 for 32 Mb MUX pSRAM
Valid Combinations	Corrected pSRAM type for S71VS064RB0 from CustComspec_01 to SWM032D108M1R Added OPNs: S71VS064RB0AHT0L S71VS256RD0AHK40
Revision 10 (June 14, 2010)	
General Description	Removed S71XS256RD0 from table Unified data sheet reference for S29VS/XS-R Removed MUX pSRAM Type 3 Added SWM128D108M1R
Valid Combinations	Restored necessary bottom boot options. Added OPNs: S71VS256RD0AHK3L/BL/3C/BC Removed OPNs: S71VS064RB0AHT00/04 Updated MUX pSRAM Type 3 entries to the Common RAM type specifications Removed table after Figure 4.3 S71XS-R 56-ball Fine-Pitch Ball Grid Array

Section	Description
Revision 11 (July 28, 2010)	
Features	Corrected MCP BGA Packages information
Ordering Information	Corrected Package Modifier information Removed 7 inch Tape and Reel option
Valid Combinations	Corrected package information for S71VS064RB0AHT0L Added OPN S71VS064RB0AHT8L, S71VS128RC0AHKCL, S71VS256RC0AHKCL Removed OPN S71VS256RD0AHK40
MCP Block Diagram	Removed figure S71XS-R MCP Block Diagram
Connection Diagrams/Physical Dimensions	Corrected figure S71VS-R 52-ball Fine-Pitch Ball Grid Array Removed figure S71XS-R 56-ball Fine-Pitch Ball Grid Array Replaced figure RSB052—52-ball VFBGA 5.0 x 7.5 mm with RSE052—52-ball VFRBGA 6.0 x 5.0 mm Refreshed DNU/RFU/NC definitions
Revision 12 (August 27, 2010)	
Valid Combinations	Corrected package information for S71VS128RB0AHK0L/8L (RLA056) Corrected speed for OPNs S71VS256RD0AHK3L/BL to 108 MHz
Connection Diagrams	Reverted DNU balls to RFU
Physical Dimensions	Added diagram for RLA056
Revision 13 (December 9, 2010)	
Features	Added Industrial temperature
General Description	Added references to S29VS_XS-R_SP, S29VS064R_XS064R_SP, SWM032D108M3R, SWM128D108M3R
Valid Combinations	Added OPNs S71VS064RB0AHT3L/BL/0M/8M, S71VS128RB0AHK3L/BL, S71VS256RD0AHK3M, S71VS256RD0AHK40/C0 Added Temperature Range Column
Revision 14 (April 13, 2011)	
General Description	Removed SWM032D108M1N and SWM064D108M1N references
Valid Combinations	Removed OPNs S71VS064RB0AHT3M/BM, S71VS128RB0AHK2L/AL, S71VS128RC0AHK20, S71VS128RC0ZHKxx, S71VS256RC0ZHKxx, S71VS256RD0ZHExx Physical Dimensions: Removed NLB056 and NSD056 diagrams. Added diagram for RLG052
Revision 15 (June 20, 2011)	
Valid Combinations	Added OPNs S71VS128RB0AHK4L/CL, , S71VS064RB0AHT4L/CL
Revision 16 (June 29, 2012)	
Valid Combinations	Added OPNs S71VS064RB0AHT3M/BM
Revision 17 (October 2, 2012)	
Valid Combinations	Updated the S71VS256RC0AHK4L/CL package from RSD056 to RLA056

Colophon

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